

SAMYANG ELECTRONICS MBR2020CT --- MBR20200CT

TO-263

0.360(9.14)

0.320(8.13)

0.053(1.34) 0.047(1.20)

0.095(2.41)

0.083(2.10

VOLTAGE RANGE: 20 --- 300 V

0.420(10.67)

0.245(6.22) MIN

2

CURRENT:20.0A

D2PAK

0.639(16.22) 0.560(14.22)

0.037(0.94) 0.027(0.69)

Dimensions in inches and (millimeters)

0.131(3.32)

0.090(2.29) 0.134(3.40)

0.105(2.67)

0. 190 (4. 83)

<u>↓</u> 0.055(1.40) <u>↓</u> 0.045(1.14)

0.066(1.68)

0.018(0.46)

0.014(0.35)

SCHOTTKY BARRIER RECTIFIER

FEATURES

- \bigotimes Metal-semiconductor junction with guard ring
- \bigcirc Epitaxial construction
- $\diamondsuit\ensuremath{\mathsf{Low}}$ forward voltage drop,low switching losses
- \bigcirc High surge capability
- ◇ For use in low voltage, high frequency inverters free wheeling, and polarity protection applications
- \bigcirc The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- - MIL-STD-202,Method 208
- ◇Polarity: As marked
- ♦ Weight: 0.08ounces, 2.24 grams
- ♦ Mounting position: Any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

	Symbols	MBR 2020CT	MBR 2030CT	MBR 2040CT	MBR 2050CT	MBR 2060CT	MBR 2080CT	MBR 20A0CT	MBR 20150CT	MBR 20200CT	Units
Maximum repetitive peak reverse voltage	VRRM	20	30	40	50	60	80	100	150	200	Volts
Maximum RMS voltage	Vrms	14	21	28	35	42	56	70	105	140	Volts
Maximum DC blocking voltage	VDC	20	30	40	50	60	80	100	150	200	Volts
Maximum average forwardPer legrectified current(see Fig.1)Total device	(A) (10.0 20.0									Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	IFSM	200.0							Amps		
Maximum instantaneous forward voltage at 20.0 A	VF	0.60			0.3	75	0	.85	0. 90	0. 95	Volts
$\begin{array}{c c} \mbox{Maximum instantaneous reverse} & $T_c=25^{\circ}C$ \\ \mbox{current at rated DC blocking} \\ \mbox{voltage(Note 1)} & $T_c=125^{\circ}C$ \\ \end{array}$	- IR	0.2 30 50							mA		
Typical thermal resistance (Note 2)	R _θ JC	3. 0									°C/W
Operating junction temperature range	TJ	-65 to+150									°C
Storage temperature range	Tsig	-65 to+150									°C

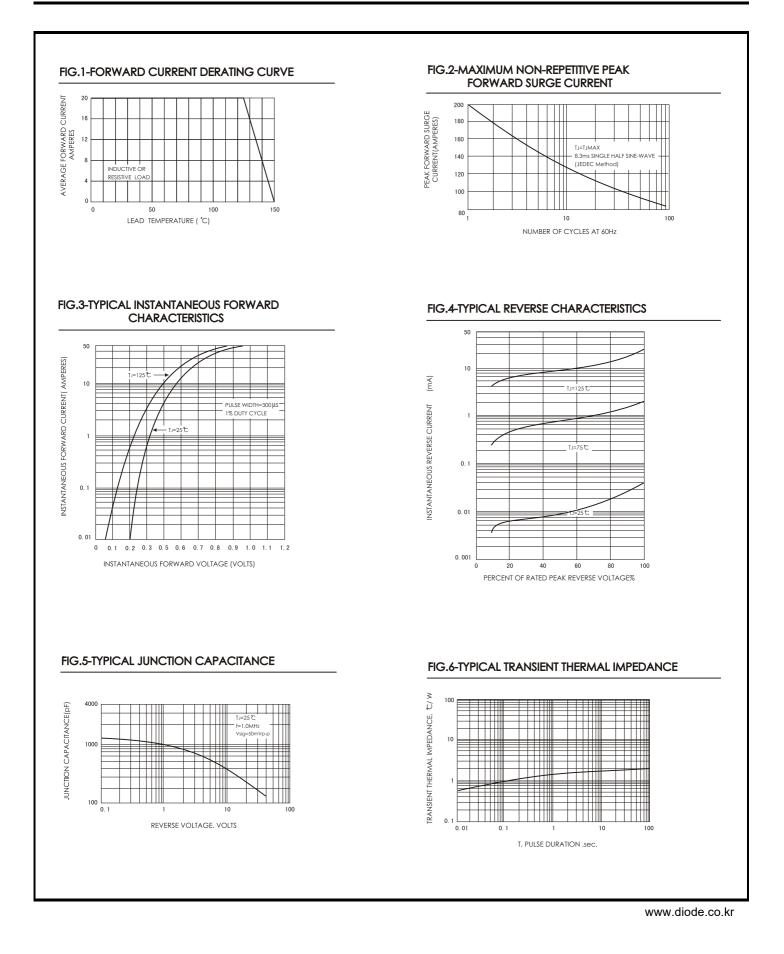
NOTE: 1. Pulse test: 300us pulse width, 1% duty cycle.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

3. Thermal resistance junction to ambient

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RATINGS AND CHARACTERISTIC CURVES



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